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N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)	
60	0.072 at V _{GS} = 10 V	5	

FEATURES

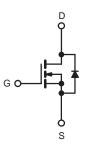
- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



RoHS COMPLIANT



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Continuous Drain Current (T _{.I} = 175 °C) ^a	T _A = 25 °C	I _D	5		
Continuous Diam Current (1) = 175 C)	T _A = 70 °C		3.1	Α	
Pulsed Drain Current		I _{DM}	20	1	
Avalanche Current		I _{AS}	4.8		
Single Pulse Avalanche Energy		E _{AS}	8	mJ	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	3.3	W	
Maximum Power Dissipation	T _A = 70 °C	. п	2.3	• • • • • • • • • • • • • • • • • • • •	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana la Ambiant	t ≤ 10 s	R _{thJA}	36	45	°C/W
Maximum Junction-to-Ambient ^a	Steady State		75	90	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	17	20	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



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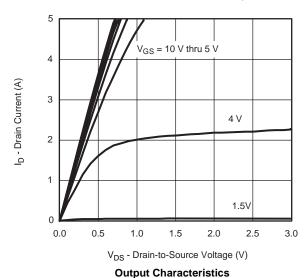
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					•		
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60	60		V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Cata Maltana Busin Comment	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			20	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
Davis Ossans Os Otata Basista and	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$		0.072	0.089	9	
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}, T_J = 125 ^{\circ}\text{C}$		0.090	0.120	Ω	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 3 \text{ A}$		7		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Dynamic ^b					•		
Total Gate Charge	Q_g			16	27		
Gate-Source Charge	Q _{gs} Q _{gd}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$		3.5		nC	
Gate-Drain Charge				5.1			
Gate Resistance	R_g	$V_{GS} = 0.1 \text{ V, f} = 5 \text{ MHz}$	0.5	1.4	2.4	Ω	
Turn-On Delay Time	t _{d(on)}			12	20		
Rise Time	t _r	V_{DD} = 30 V, R_L = 30 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 3 A$, $V_{GEN} = 10 V$, $R_g = 6 \Omega$		28	50	ns	
Fall Time	t _f			12	24		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 3 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		55	80		

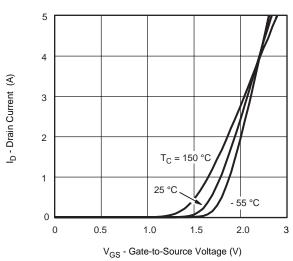
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





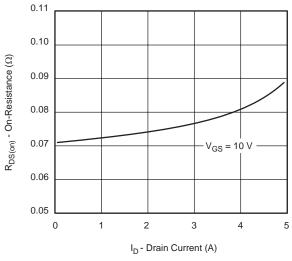
Transfer Characteristics



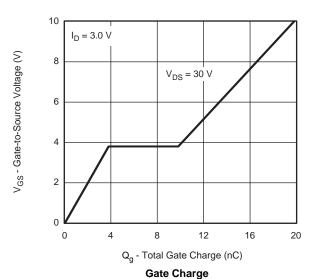
I_S - Source Current (A)

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On-Resistance vs. Drain Current



T_J = 175 °C $T_{J} = 175$ °C $T_{J} = 25$ °C

0.0

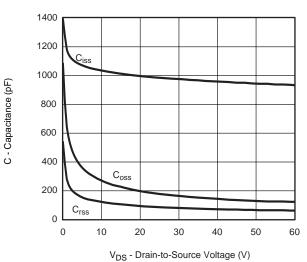
0.7

0.8

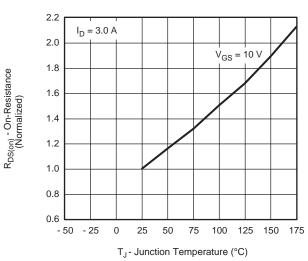
0.9

1.1 V_{SD} - Source-to-Drain Voltage (V)

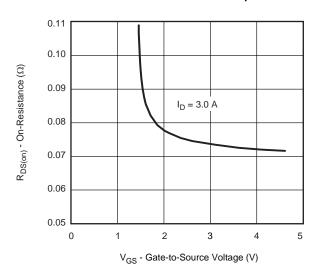
Source-Drain Diode Forward Voltage



Capacitance



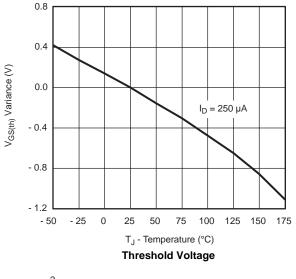
On-Resistance vs. Junction Temperature

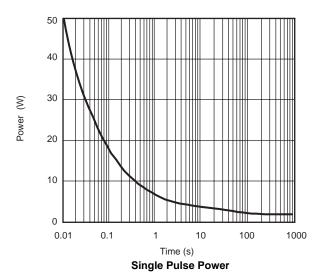


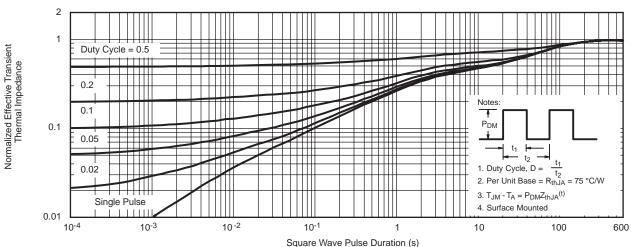
On-Resistance vs. Gate-to-Source Voltage

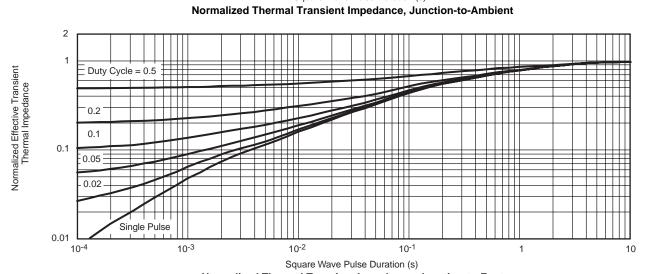


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted













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